

FOR IMMEDIATE RELEASE
November 6, 2007

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GaN on Si RF power transistor manufacturer Nitronex qualifies new wafer fab...

NITRONEX QUALIFIES NEW WAFER FAB FOR VOLUME PRODUCTION

Durham, N.C. (November 6, 2007) — Nitronex, the global leader in gallium nitride on silicon (GaN on Si) RF power transistors for the wireless infrastructure, broadband and military markets, has qualified its new, state-of-the-art manufacturing facility. The move from Raleigh to Durham began in first quarter 2007 and was finished in the second quarter, with qualification testing completed in October. The completed qualification verifies that Nitronex has successfully replicated the process developed in Raleigh at the new Durham fab and is prepared for volume production. A summary of Nitronex's fabrication qualification report will be available in late November.

“Completing rigorous qualification verifies that the material produced in the new Durham facility matches material produced in Raleigh. The data for parts generated in Durham show the same reliability and performance when compared to products from our Raleigh facilities,” said Bruce Cochran, Nitronex VP of Operations. “This is a milestone for the company, and is further evidence that we have evolved from pilot line production to volume manufacturing.”

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NITRONEX QUALIFIES FABRICATION PROCESS FOR VOLUME PRODUCTION, PAGE 2

The successful qualification completes the relocation of the company into its new 85,000 square-foot R&D and manufacturing facility. This move enhances Nitronex's current and future manufacturing capacity and capability, while also providing additional space for expanding research and development efforts.

For more information about Nitronex's GaN on Si manufacturing processes and broad product offering, contact Nitronex at 2305 Presidential Drive, Durham, NC 27703; call 919-807-9100; or e-mail info@nitronex.com.

About Nitronex

Specializing in the development and manufacturing of gallium nitride (GaN) RF power devices, Nitronex is the global leader in high-performance GaN on silicon (GaN on Si) RF power transistors for the commercial wireless infrastructure, broadband and military markets. Based on its patented SIGANTIC[®] process — gallium nitride on silicon technology — Nitronex is at the forefront of commercializing GaN technology for RF applications. The company's ability to combine the disciplines of material growth, wafer processing, device design and wireless applications knowledge is unique to the industry.

Nitronex was founded in 1999 by graduates of the wide bandgap program at North Carolina State University and is headquartered in Durham, North Carolina. It holds 19 patents with 19 others pending.

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